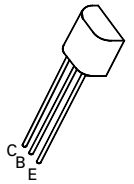
PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

2N6728
2N6729
2N6730

ISSUE 1 – MARCH 94

FEATURES

* 100 Volt V_{CEO}
* Gain of 20 at I_C = 0.5 Amp
* P_{tot}=1 Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	2N6728	2N6729	2N6730	UNIT
Collector-Base Voltage	V_{CBO}	-60	-80	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	-100	V
Emitter-Base Voltage	V_{EBO}	-5			V
Peak Pulse Current	I_{CM}	-2			A
Continuous Collector Current	I_C	-1			A
Power Dissipation at T_{amb}= 25°C	P_{tot}	1			W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200			°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	2N6728		2N6729		2N6730		UNIT	CONDITIONS.
		MIN.	MAX	MIN.	MAX	MIN.	MAX		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		-80		-100		V	I_C=-0.1mA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60		-80		-100		V	I_C=-1mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		-5		V	I_E=-1mA, I_C=0
Collector Cut-Off Current	I_{CBO}		-1		-1		-1	µA µA µA	V_{CB}=-60V, I_E=0 V_{CB}=-80V, I_E=0 V_{CB}=-100V, I_E=0
Emitter Cut-Off Current	I_{EBO}		-1		-1		-1	µA	V_{EB}=-5V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5 -0.35		-0.5 -0.35		-0.5 -0.35	V	I_C=-250mA,I_B=-10mA* I_C=-250mA,I_B=-25mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2		-1.2		-1.2	V	IC=-250mA, V_{CE}=-1V*
Static Forward Current Transfer Ratio	h_{FE}	80 50 20	250	80 50 20	250	80 50 20	250		I_C=-50mA, V_{CE}=-1V* I_C=-250mA, V_{CE}=-1V* I_C=-500mA, V_{CE}=-1V*
Transition Frequency	f_T	50	500	50	500	50	500	MHz	I_C=-50mA, V_{CE}=-10V
Collector Base Capacitance	C_{CB}		30		30		30	pF	V_{CE}=-10V, f=1MHz